Product data sheet

1. Product profile

1.1 General description

Planar passivated ultra sensitive gate Silicon Controlled Rectifier in a SOT54 (T0-92) plastic package.

1.2 Features and benefits

- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Ultra sensitive gate

1.3 Applications

- Electronic ballasts
- Safety shut down and protection circuits
- Sensing circuits
- Smoke detectors
- Switched Mode Power Supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25$ °C; $t_p = 10$ ms; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	-	8	Α
I _{T(AV)}	average on-state current	half sine wave; T _{lead} ≤ 67 °C; see <u>Figure 3</u>	-	-	0.51	Α
I _{T(RMS)}	RMS on-state current	half sine wave; T _{lead} ≤ 67 °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	8.0	Α
Static characteristics						
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 10 \text{ mA;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{ or } 100 \text{ me}}$	0.5	-	7	μΑ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol		
1	Α	anode		. 81		
2	G	gate		A - K		
3	K	cathode		G Sym037		
			SOT54 (TO-92)			

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
N0118GA	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

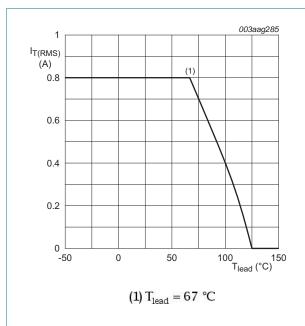
4. Limiting values

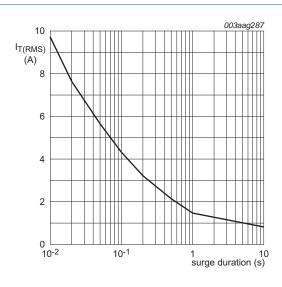
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Min	Max	Unit
repetitive peak off-state voltage		-	600	V
repetitive peak reverse voltage		-	600	V
average on-state current	half sine wave; T _{lead} ≤ 67 °C; see <u>Figure 3</u>	-	0.51	Α
RMS on-state current	half sine wave; $T_{lead} \le 67$ °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	0.8	Α
non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 10 \text{ ms}$; see Figure 4; see Figure 5	-	8	Α
	half sine wave; $T_{j(init)} = 25$ °C; $t_p = 8.3$ ms	-	9	Α
I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	0.32	A^2s
rate of rise of on-state current	$I_T = 0.8 \text{ A}$; $I_G = 10 \text{ mA}$; $dI_G/dt = 0.1 \text{ A/}\mu\text{s}$	-	50	A/µs
peak gate current		-	1	Α
peak reverse gate voltage		-	5	V
peak gate power		-	2	W
average gate power	over any 20 ms period	-	0.1	W
storage temperature		-40	150	°C
junction temperature		-	125	°C
	repetitive peak off-state voltage repetitive peak reverse voltage average on-state current RMS on-state current non-repetitive peak on-state current I²t for fusing rate of rise of on-state current peak gate current peak reverse gate voltage peak gate power average gate power storage temperature	repetitive peak off-state voltage repetitive peak reverse voltage average on-state current half sine wave; $T_{lead} \le 67 ^{\circ}\text{C}$; see Figure 3 RMS on-state current half sine wave; $T_{lead} \le 67 ^{\circ}\text{C}$; see Figure 1; see Figure 2 half sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 10 \text{ms}$; see Figure 4; see Figure 5 half sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 8.3 \text{ms}$ $t_p = 10 \text{ms}$; sine-wave pulse rate of rise of on-state current $t_p = 10 \text{ms}$; sine-wave pulse peak gate current peak reverse gate voltage peak gate power average gate power over any 20 ms period storage temperature	repetitive peak off-state voltage repetitive peak reverse voltage average on-state current half sine wave; $T_{lead} \le 67$ °C; see Figure 3 RMS on-state current half sine wave; $T_{lead} \le 67$ °C; see Figure 1; see Figure 2 non-repetitive peak on-state current half sine wave; $T_{j(init)} = 25$ °C; $t_p = 10$ ms; see Figure 4; see Figure 5 half sine wave; $T_{j(init)} = 25$ °C; $t_p = 8.3$ ms $I^{2}t \text{ for fusing} \qquad t_p = 10 \text{ ms; sine-wave pulse} \qquad -$ rate of rise of on-state current $I_T = 0.8 \text{ A}; I_G = 10 \text{ mA}; \text{ dI}_G/\text{dt} = 0.1 \text{ A}/\mu\text{s} \qquad -$ peak gate current peak reverse gate voltage peak gate power average gate power over any 20 ms period -40	repetitive peak off-state voltage - 600 repetitive peak reverse voltage - 600 average on-state current half sine wave; $T_{lead} \le 67 ^{\circ}\text{C}$; see Figure 3 - 0.51 RMS on-state current half sine wave; $T_{lead} \le 67 ^{\circ}\text{C}$; see Figure 1; see Figure 2 half sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 10 \text{ms}$; see Figure 4; see Figure 5 half sine wave; $t_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 8.3 \text{ms}$ - 9 l²t for fusing $t_p = 10 \text{ms}$; sine-wave pulse - 0.32 rate of rise of on-state current $t_p = 10 \text{ms}$; sine-wave pulse - 1 peak gate current peak reverse gate voltage - 5 peak gate power over any 20 ms period - 0.1 storage temperature - 40 150





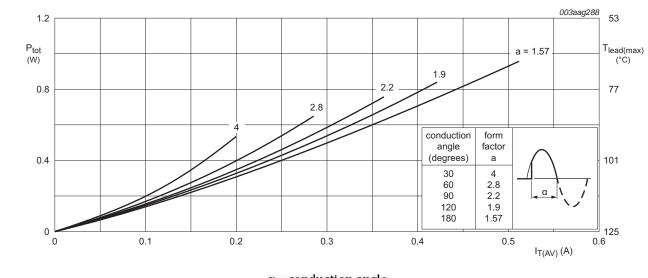


$$f = 50 \text{ Hz}$$

 $T_{lead} = 67 \text{ °C}$

Fig 1. RMS on-state current as a function of lead temperature; maximum values

Fig 2. RMS on-state current as a function of surge duration; maximum values



$$\begin{split} \alpha &= conduction \ angle \\ a &= form \ factor = I_{T(RMS)} \, / \, I_{T(AV)} \end{split}$$

Fig 3. Total power dissipation as a function of average on-state current; maximum values

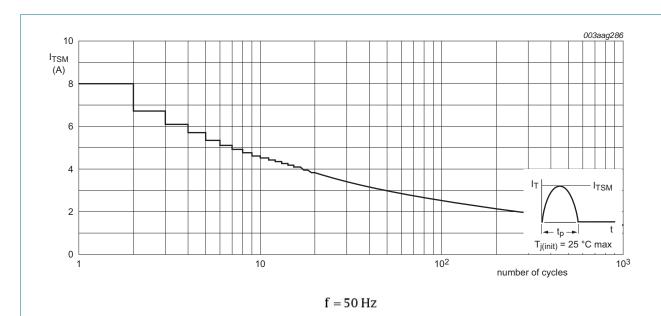


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

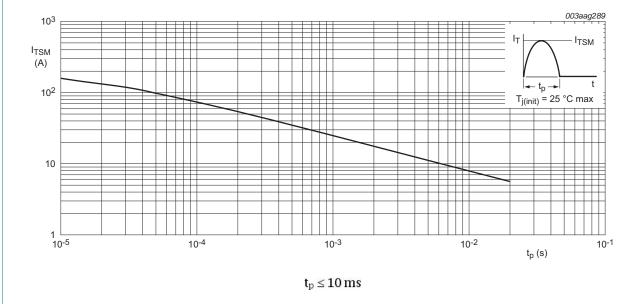
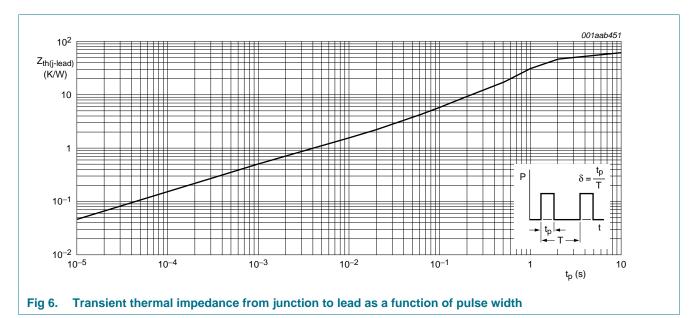


Fig 5. Non-repetitive peak on-state current as a function of pulse duration; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance from junction to lead	see Figure 6	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W



6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static characteristics						
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 \text{ °C};$ see Figure 7	0.5	-	7	μΑ
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 8</u>	-	-	6	mA
I _H	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{\text{see Figure 10}};$	-	-	5	mA
V_{T}	on-state voltage	$I_T = 1.6 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 11}{\text{M}}$	-	1.4	1.95	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u>	-	-	8.0	V
I _D	off-state current	$V_D = 600 \text{ V}; T_j = 25 \text{ °C}; R_{GK} = 1 \text{ k}\Omega$	-	-	10	μΑ
		$V_D = 600 \text{ V}; T_j = 125 \text{ °C}; R_{GK} = 1 \text{ k}\Omega$	-	-	100	μΑ
I _R	reverse current	T_j = 25 °C; R_{GK} = 1 $k\Omega$; V_R = 600 V	-	-	10	μA
		$T_j = 125 ^{\circ}C; R_{GK} = 1 k\Omega; V_R 600 V$	-	-	100	μA
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; R_{GK} = 1 k Ω ; exponential waveform; see <u>Figure 13</u> ; see <u>Figure 14</u>	75	-	-	V/µs

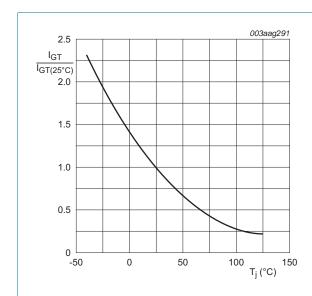


Fig 7. Normalized gate trigger current as a function of junction temperature

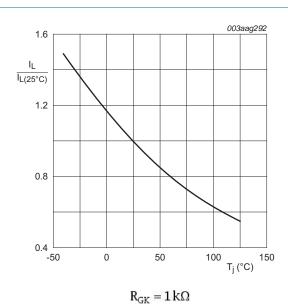


Fig 8. Normalized latching current as a function of junction temperature

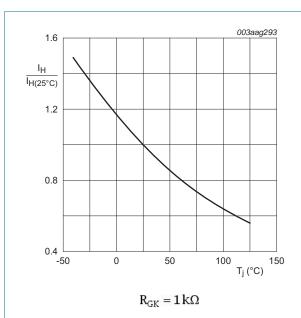
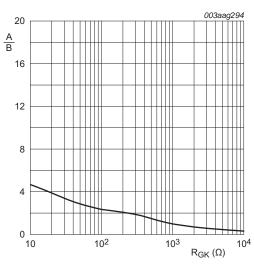
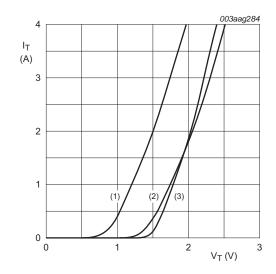


Fig 9. Normalized holding current as a function of junction temperature



$$\begin{aligned} A &= I_H \; \big[R_{GK} \big] \\ B &= I_H \; \big[R_{GK} = 1 \, k \Omega \big] \\ T_i &= 25 \; ^{\circ}\mathrm{C} \end{aligned}$$

Fig 10. Normalized holding current as a function of gate-cathode resistance (typical values)



 $V_0 = 1.383 \, V; \, R_s = 0.40 \, \Omega$ (1) $T_j = 125 \, ^{\circ}C; \, typical \, values$

(2) $T_j = 125$ °C; maximum values

(3) $T_j = 25$ °C; maximum values

Fig 11. On-state current as a function of on-state voltage

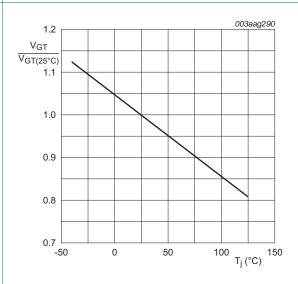
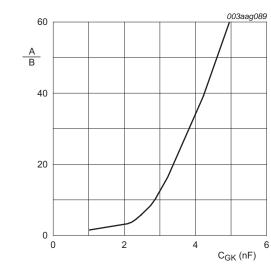
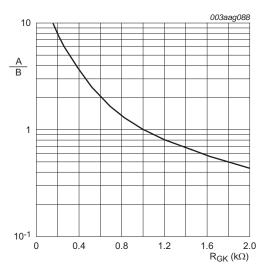


Fig 12. Normalized gate trigger voltage as a function of junction temperature



$$\begin{split} A &= \frac{dV}{dt} \left[C_{GK} \right] \\ B &= \frac{dV}{dt} \left[R_{GK} = 1 \, k\Omega \right] \\ T_j &= 125 \, ^{\circ}C; R_{GK} = 1 \, k\Omega; V_{DM} = 402 \, V \end{split}$$

Fig 13. Normalized dVd/dt immunity as a function of gate-cathode capacitance (typical values)



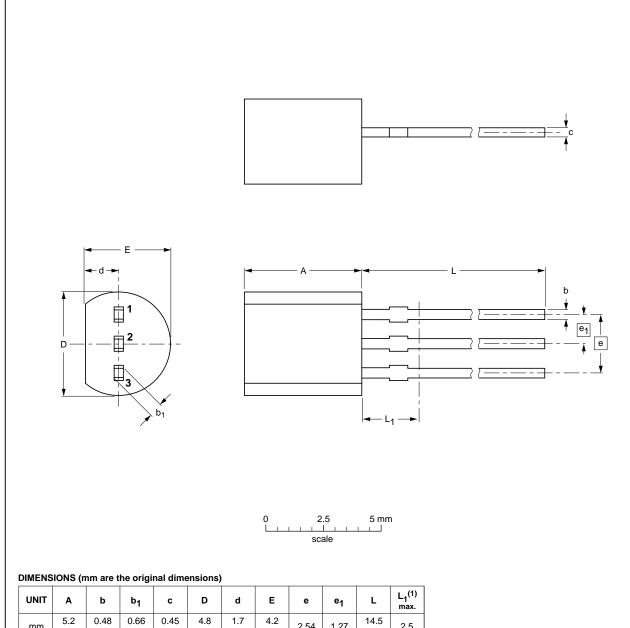
$$\begin{split} A &= \frac{dV}{dt} \left[R_{GK} \right] \\ B &= \frac{dV}{dt} \left[R_{GK} = 1 \, k\Omega \right] \\ T_j &= 125 \, ^{\circ}\text{C}; V_{DM} = 402 \, V \end{split} \label{eq:approximation}$$

Fig 14. Normalized dVd/dt immunity as a function of gate-cathode resistance (typical values)

Package outline

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ('') max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
	TO-92	SC-43A		04-06-28 04-11-16
_	IEC			

Fig 15. Package outline SOT54 (TO-92)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
N0118GA v.1	20110711	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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